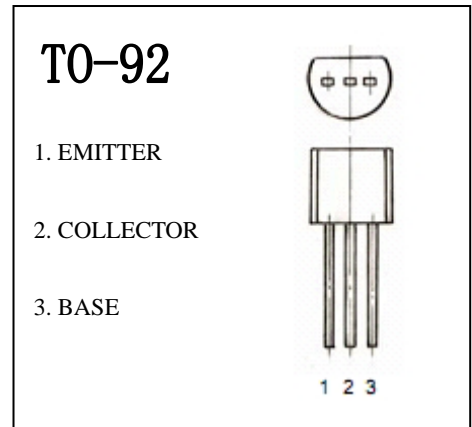




M28S TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	40	V
VCEO	Collector-Emitter Voltage	20	V
VEBO	Emitter-Base Voltage	6	V
IC	Collector Current	1.0	A
PC	Collector Power Dissipation	625	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specjied):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =100μA, I _E =0	40			V
Collector-emittre breakdown' voltage	V(BR) _{CEO}	I _C =1mA, I _B =0	20			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _C =100μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			1.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	H _{FE}	V _{ce} =1V, I _c =100mA	300		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =600mA, I _B =20mA			0.55	V
Transition Frequency	f _T	V _{CE} =10V, I _C =50mA, f=30MAZ	100			MHZ